Silicon Carbide Schottky Diode

650 V, 40 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 95 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



ON Semiconductor®

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V _{RRM}	I _F	
650 V	40 A	



Case

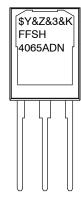
ode/ 3

3. Anode



TO-247-3LD CASE 340CH

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code

&K = Lot Code

FFSH4065ADN = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH4065ADN-F155	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)	se Avalanche Energy (Note 1)		mJ
I _F	Continuous Rectified Forward Current			Α
	Continuous Rectified Forward Current			
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	Tc = 25°C, 10 μs	1100	Α
		Tc = 150°C, 10 μs	1000	Α
I _{F, SM}	Non-Repetitive Forward Surge Current	Forward Surge Current		Α
I _{F, RM}	Repetitive Forward Surge Current		58	Α
P _{tot}	Power Dissipation	Tc = 25°C	150	W
		Tc = 150°C	25	W
T _J , T _{STG}	Operating and Storage Temperature Range	uting and Storage Temperature Range		°C
	TO247 Mounting Torque, M3 Screw		60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Rating	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.	1.0* / 0.5**	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH4065ADN-F155	FFSH4065ADN	TO-247 Long Lead	Tube	N/A	N/A	30 Units

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _F	Forward Voltage	IF = 20 A, Tc = 25°C	-	1.5	1.75	V
		IF = 20 A, Tc = 125°C	-	1.6	2.0	
		IF = 20 A, Tc = 175°C	-	1.72	2.4	
I _R	Reverse Current	VR = 650 V, Tc = 25°C	-	-	200	μΑ
		VR = 650 V, Tc = 125°C	-	-	400	
		VR = 650 V, Tc = 175°C	-	-	600	
Q _C	Total Capacitance Charge	V = 400 V	-	64	-	nC
С	Total Capacitance	VR = 1 V, f = 100 kHz	-	1085	-	pF
		VR = 200 V, f = 100 kHz	-	117	-	
		VR = 400 V, f = 100 kHz	-	88	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{*}Per leg.

^{**}Per Device.

^{1.} E_{AS} of 95 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 19.5 A, V = 50 V.

TYPICAL CHARACTERISTICS

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

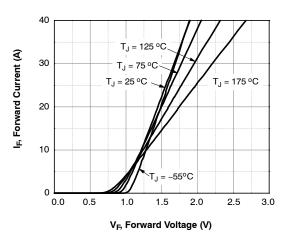


Figure 1. Forward Characteristics

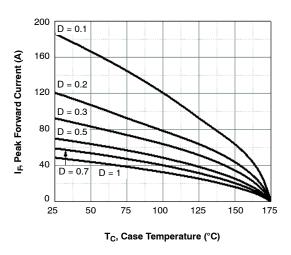


Figure 3. Current Derating

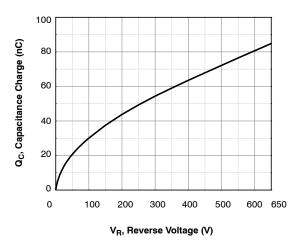


Figure 5. Capacitive Charge vs. Reverse Voltage

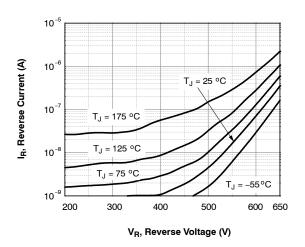


Figure 2. Reverse Characteristics

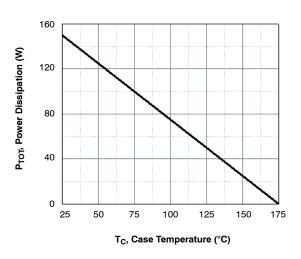


Figure 4. Power Derating

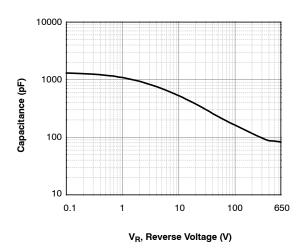


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS (Continued)

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

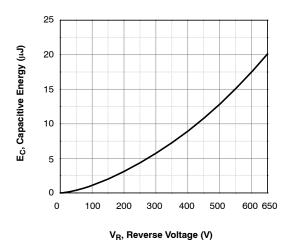


Figure 7. Capacitance Stored Energy

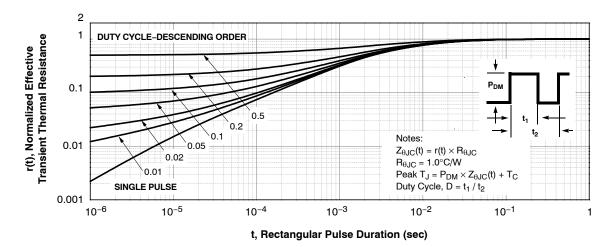
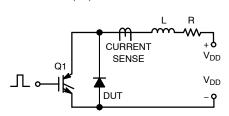


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$$\label{eq:local_local_local} \begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \ \Omega \\ V_{DD} &= 50 \ V \\ EAVL &= 1/2 LI2 \left[V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right] \\ Q1 &= IGBT \left(BV_{CES} > DUT \ V_{R(AVL)} \right) \end{split}$$



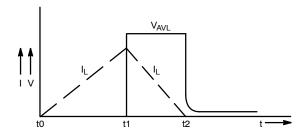
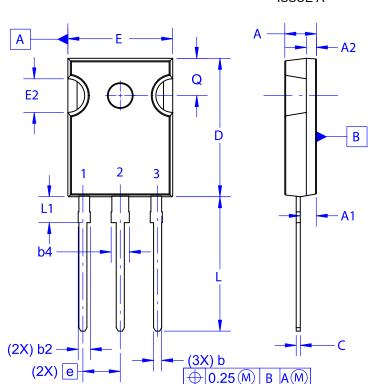


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

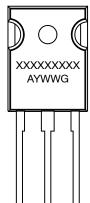
TO-247-3LD CASE 340CH **ISSUE A**





- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
 D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC **MARKING DIAGRAM***



XXXX = Specific Device Code

= Assembly Location

WW = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

	DATE 0	9 OCT 2019
Ø P —		Ø P1 D2
S E1 —	2	D1
•		,

DIM	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A 1	2.29	2.475	2.66	
A2	1.40	1.50	1.60	
D	20.32	20.57	20.82	
Е	15.37	15.62	15.87	
E2	4.96	5.08	5.20	
е	~	5.56	?	
L	19.75	20.00	20.25	
L1	3.69	3.81	3.93	
ØΡ	3.51	3.58	3.65	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	
Ь	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
b4	2.42	2.54	2.66	
С	0.51	0.61	0.71	
D1	13.08	~	?	
D2	0.51	0.93	1.35	
E1	12.81	~	?	
ØP1	6.61	6.73	6.85	

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